

Description

The XPX1216RX uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages. This device is suitable for use as a load switching application and a wide variety of other applications.

General Features

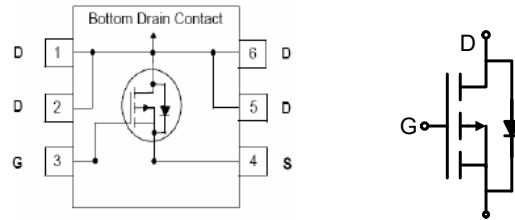
$$R_{DS(ON)} = 11m\Omega @ V_{GS} = -4.5V$$

$$R_{DS(ON)} = 14m\Omega @ V_{GS} = -2.5V$$

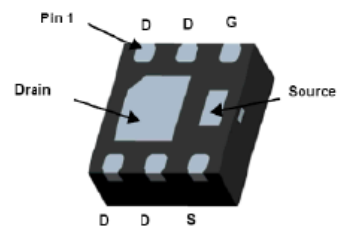
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

Application

- PWM applications
- Load switch
- Battery charge in cellular handset



Pin assignment



DFN2X2-6L bottom view

Package marking and ordering information

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
1216	1216	DFN2X2-6L	-	-	-

Absolute maximum ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-16	A
Drain Current -Pulsed (Note 1)	I_{DM}	-65	A
Maximum Power Dissipation	P_D	18	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	6.9	$^\circ C/W$
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Electrical characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-12	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-6.7A	-	11	18	mΩ
		V _{GS} =-2.5V, I _D =-6.2A	-	14	22	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-6.7A	20	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, F=1.0MHz	-	2508	-	PF
Output Capacitance	C _{oss}		-	680	-	PF
Reverse Transfer Capacitance	C _{rss}		-	590	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, I _D =-1A V _{GS} =-4.5V, R _{GEN} =10Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	35	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-6V, I _D =-10A, V _{GS} =-4.5V	-	35	48	nC
Gate-Source Charge	Q _{gs}		-	5	-	nC
Gate-Drain Charge	Q _{gd}		-	10	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-8A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-16	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Characteristics

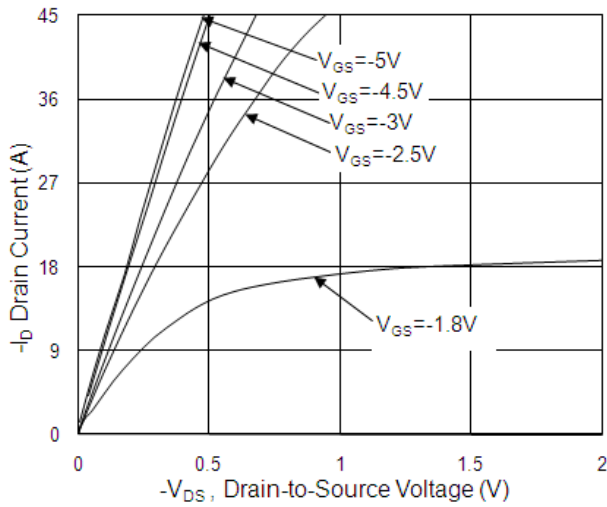


Fig.1 Typical Output Characteristics

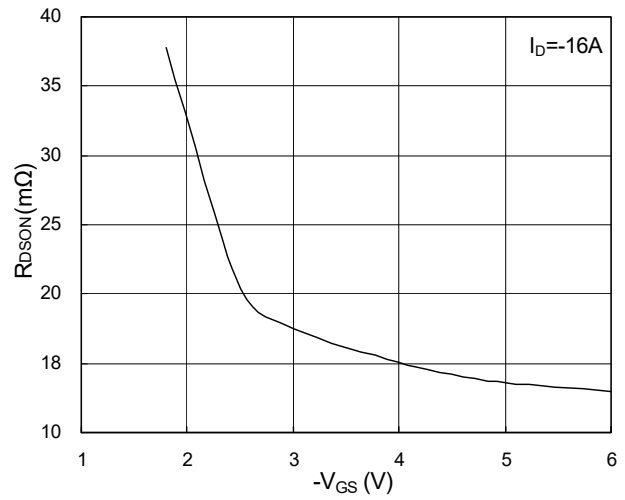


Fig.2 On-Resistance vs. Gate-Source

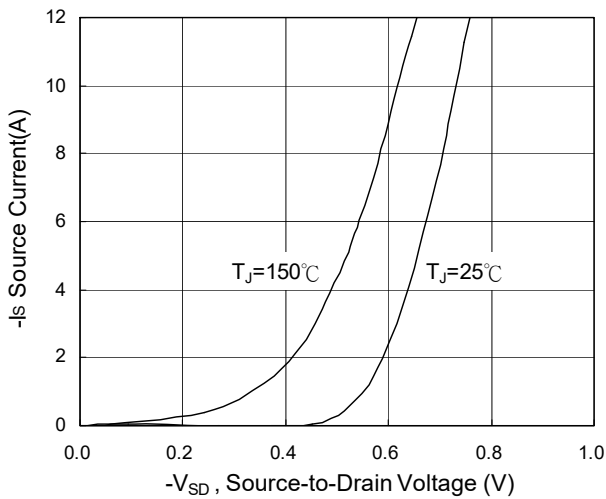


Fig.3 Forward Characteristics Of Reverse

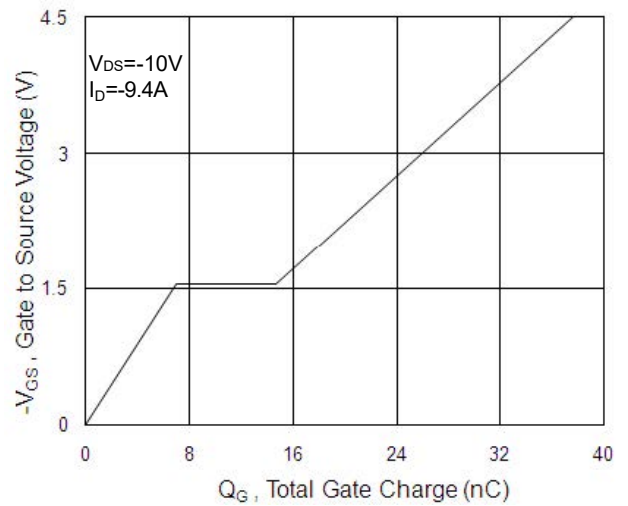


Fig.4 Gate-Charge Characteristics

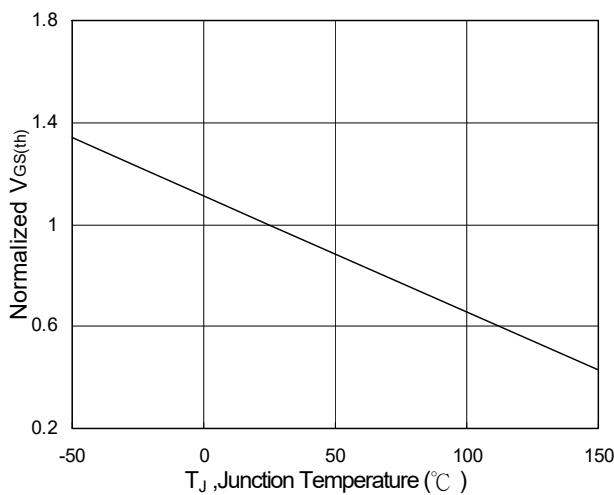


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

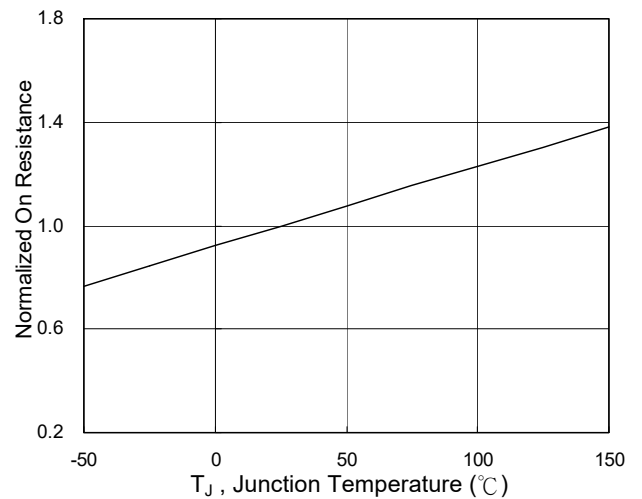


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1sec
Pb-Free device	260°C +0/-5°C	5sec ±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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